

FQP11N40C / FQPF11N40C

N-Channel QFET® MOSFET

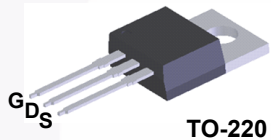
400 V, 10.5 A, 530 mΩ

Features

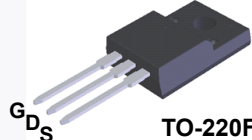
- 10.5 A, 400 V, $R_{DS(on)} = 530 \text{ m}\Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 5.25 \text{ A}$
- Low Gate Charge (Typ. 28 nC)
- Low C_{rss} (Typ. 85 pF)
- 100% Avalanche Tested

Description

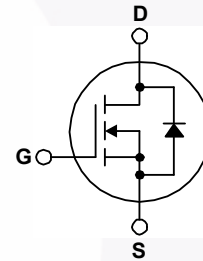
This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.



TO-220



TO-220F



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQP11N40C	FQPF11N40C	Unit
V_{DSS}	Drain to Source Voltage	400		V
I_D	Drain Current -Continuous ($T_C = 25^\circ\text{C}$) -Continuous ($T_C = 100^\circ\text{C}$)	10.5	10.5 *	A
		6.6	6.6 *	A
I_{DM}	Drain Current - Pulsed (Note 1)	42	42 *	A
V_{GSS}	Gate to Source Voltage	± 30		V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	360		mJ
I_{AR}	Avalanche Current (Note 1)	11		A
E_{AR}	Repetitive Avalanche Energy (Note 1)	13.5		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	135	44	W
		1.07	0.35	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to $+150$		$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300		$^\circ\text{C}$

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FQP11N40C	FQPF11N40C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.93	2.86	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max	62.5	62.5	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQP11N40C	FQP11N40C	TO-220	Tube	N/A	50 units
FQPF11N40C	FQPF11N40C	TO-220F	Tube	N/A	50 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	400	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.54	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 400 V, V _{GS} = 0 V	--	--	1	μA
		V _{DS} = 320 V, T _C = 125°C	--	--	10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.0	--	4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 5.25 A	--	0.43	0.53	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 5.25 A	--	7.1	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	840	1090	pF
C _{oss}	Output Capacitance		--	250	325	pF
C _{rss}	Reverse Transfer Capacitance		--	85	110	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 200 V, I _D = 10.5 A, R _G = 25 Ω (Note 4)	--	14	40	ns
t _r	Turn-On Rise Time		--	89	190	ns
t _{d(off)}	Turn-Off Delay Time		--	81	170	ns
t _f	Turn-Off Fall Time		--	81	170	ns
Q _g	Total Gate Charge	V _{DS} = 320 V, I _D = 10.5 A, V _{GS} = 10 V (Note 4)	--	28	35	nC
Q _{gs}	Gate-Source Charge		--	4	--	nC
Q _{gd}	Gate-Drain Charge		--	15	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	10.5	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	42	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 10.5 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 10.5 A, dI _F / dt = 100 A/μs	--	290	--	ns
Q _{rr}	Reverse Recovery Charge		--	2.4	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. $L = 5.7\text{ mH}$, $I_{AS} = 10.5\text{ A}$, $V_{DD} = 50\text{ V}$, $R_G = 25\text{ }\Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 10.5\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

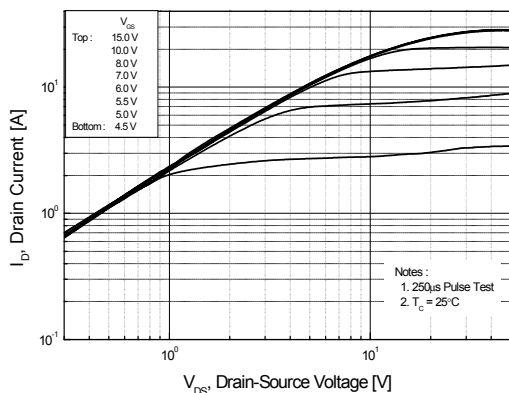


Figure 2. Transfer Characteristics

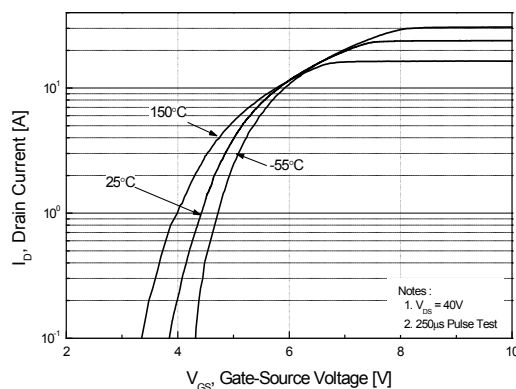


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

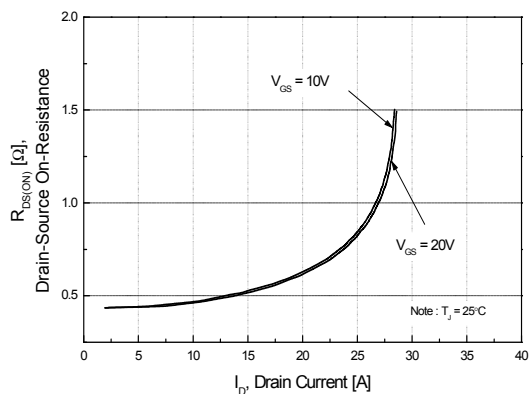


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

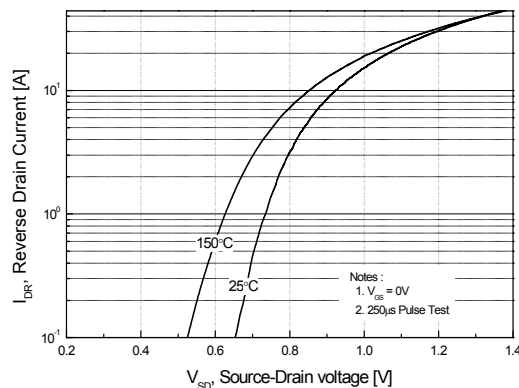


Figure 5. Capacitance Characteristics

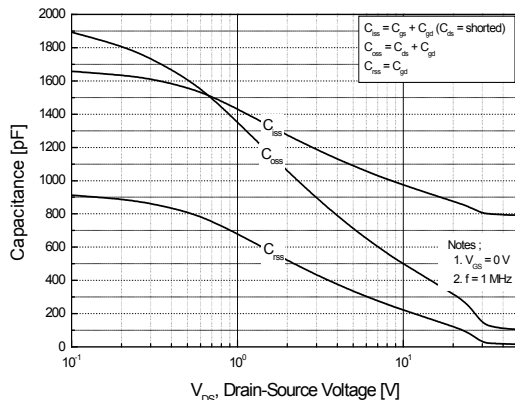
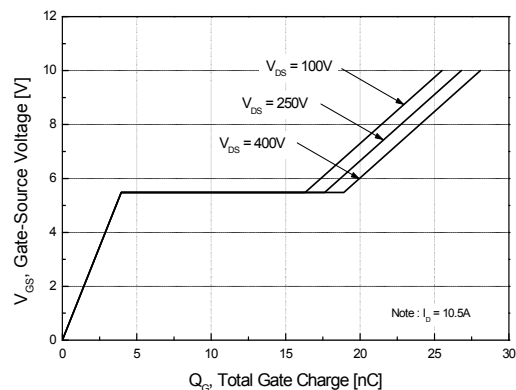


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

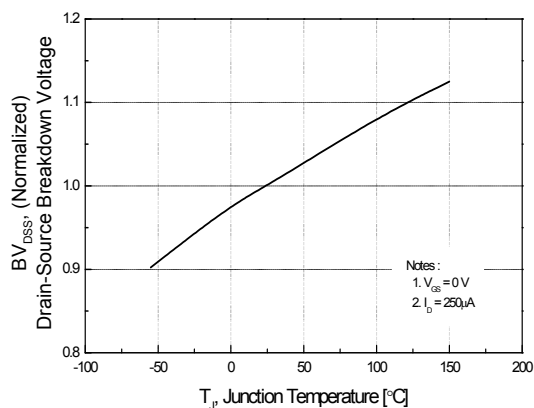


Figure 8. On-Resistance Variation vs. Temperature

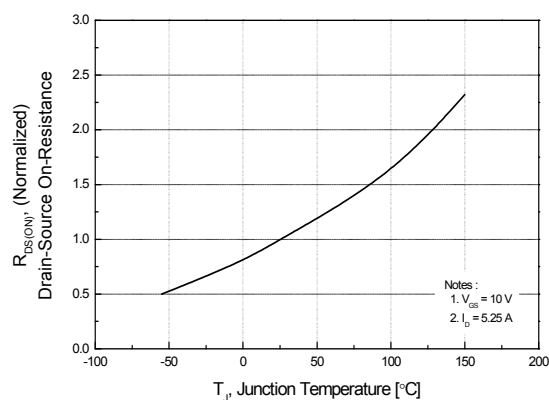


Figure 9-1. Maximum Safe Operating Area of FQP11N40C

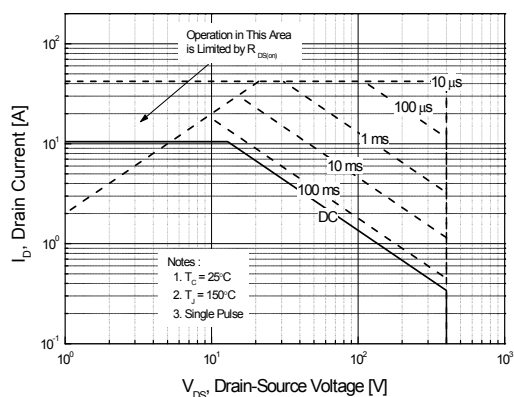


Figure 9-2. Maximum Safe Operating Area of FQPF11N40C

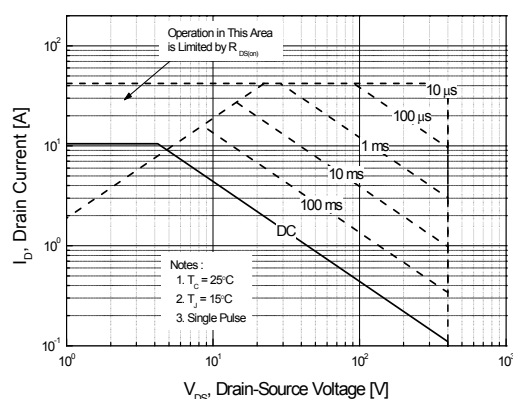
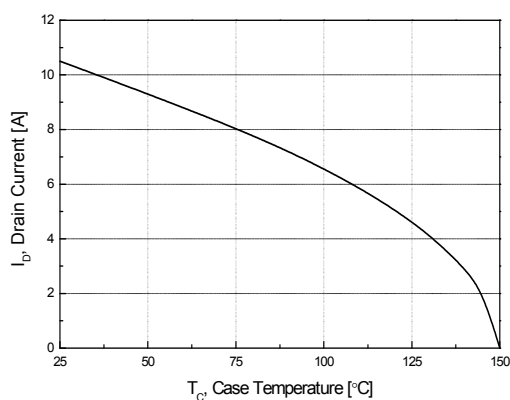


Figure 10. Maximum Drain Current



Typical Performance Characteristics (Continued)

Figure 11-1. Transient Thermal Response Curve of FQP11N40C

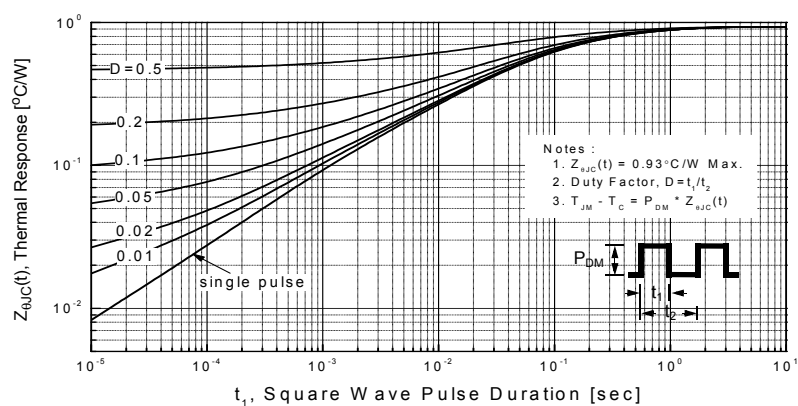


Figure 11-2. Transient Thermal Response Curve of FQPF11N40C

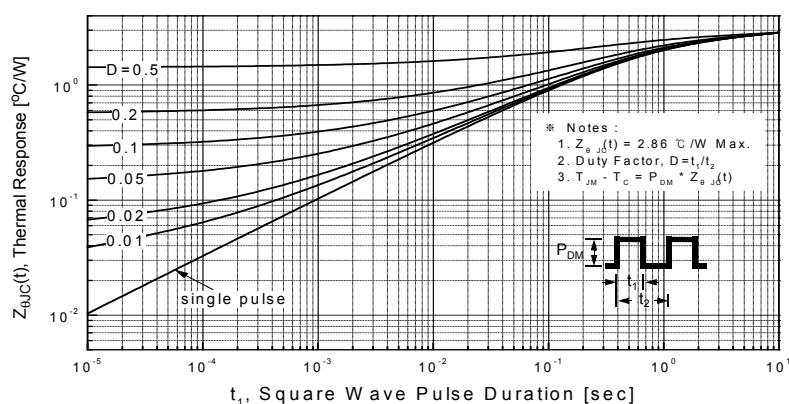


Figure 12. Gate Charge Test Circuit & Waveform

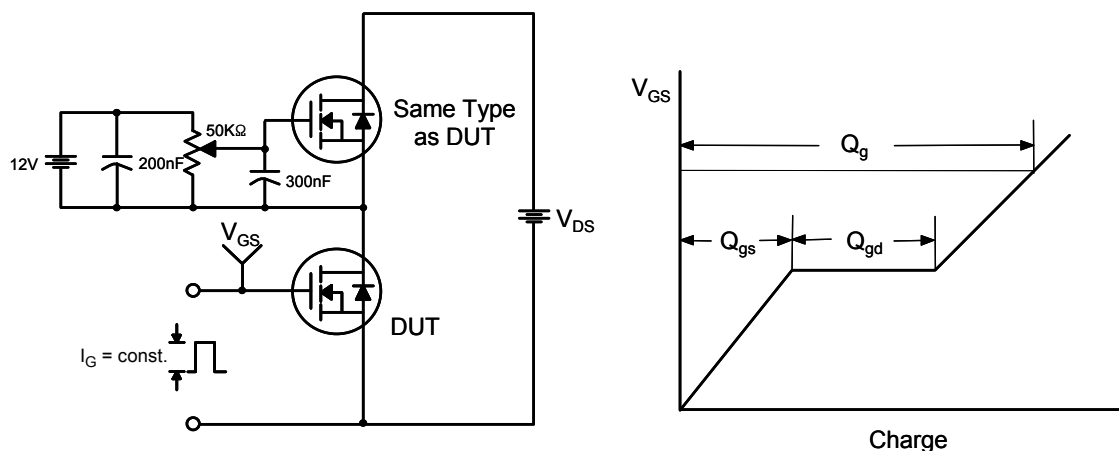


Figure 13. Resistive Switching Test Circuit & Waveforms

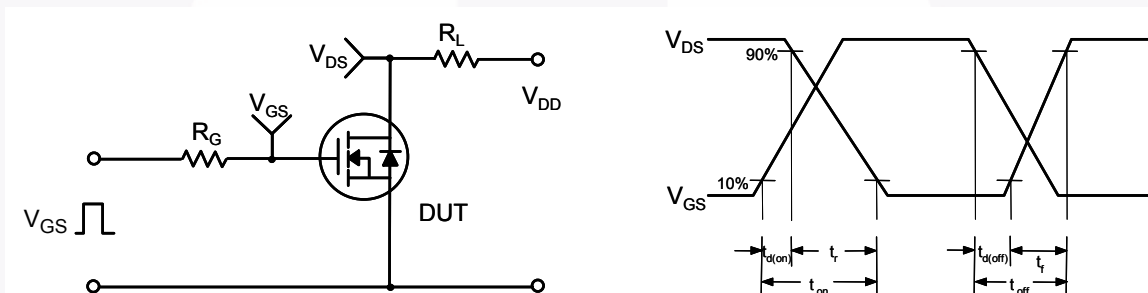


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

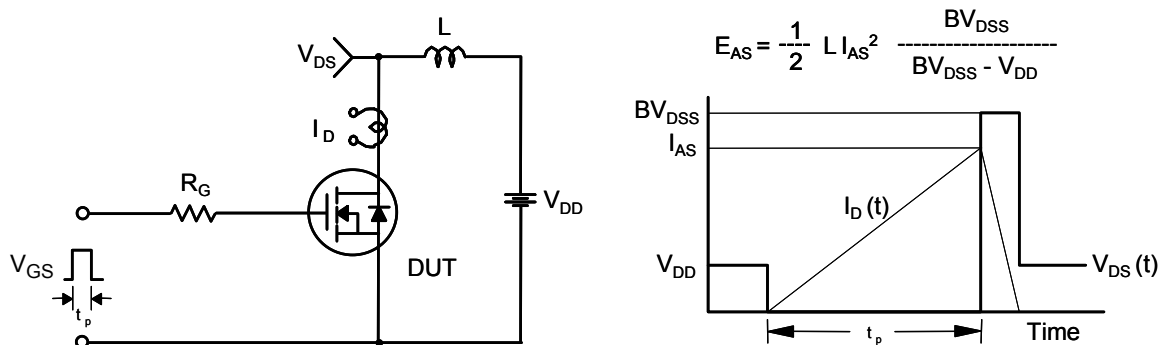
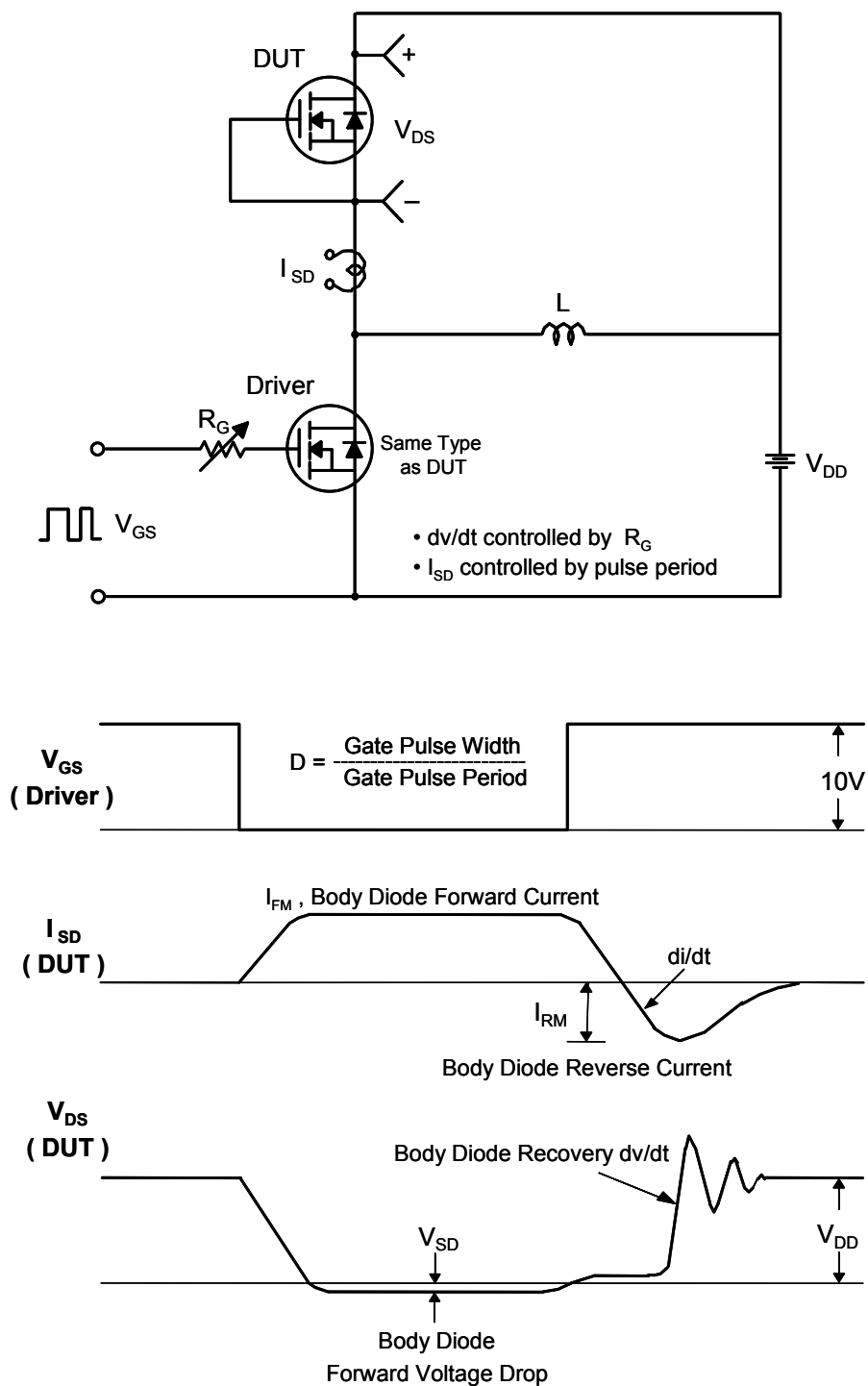


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

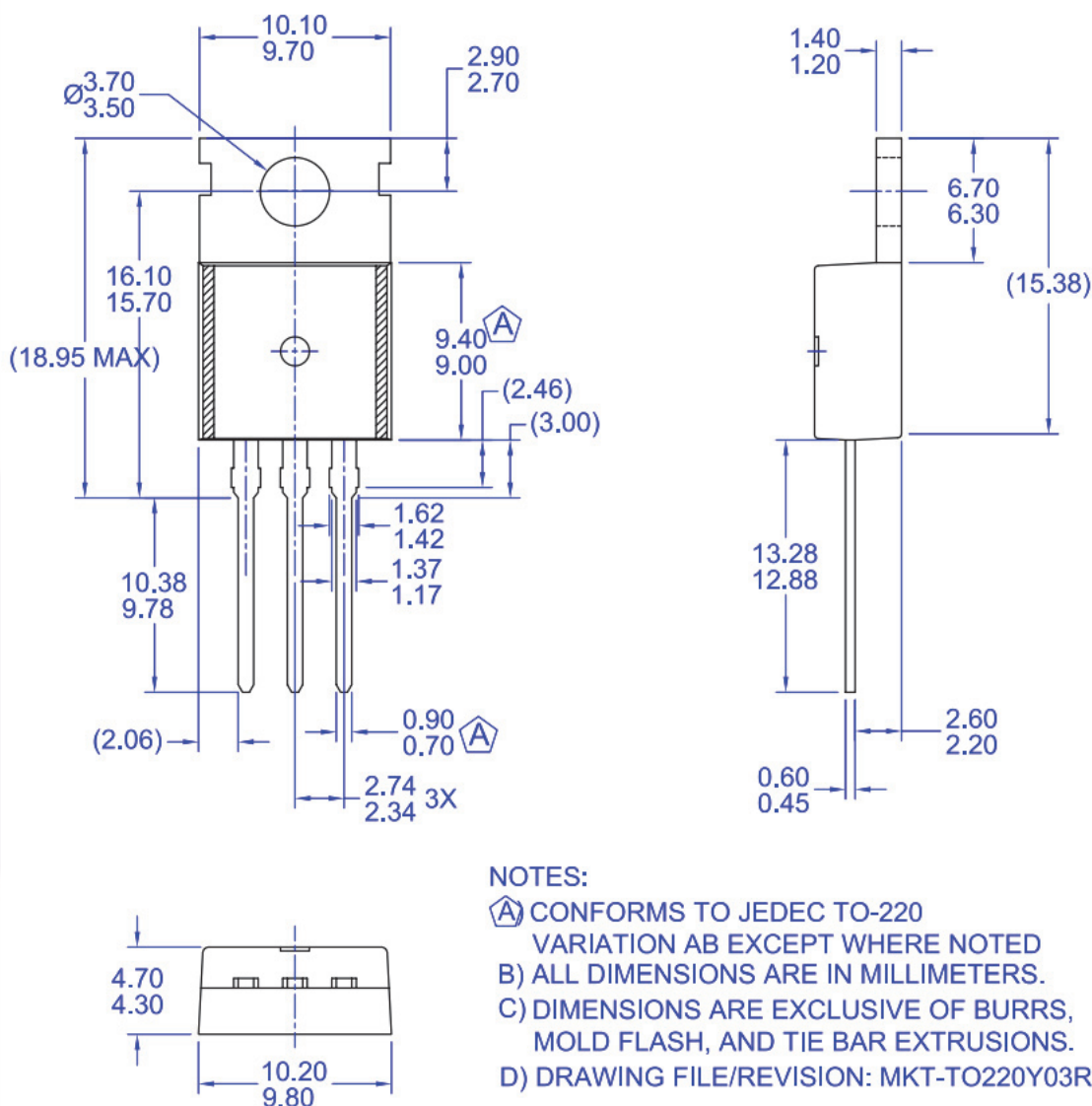


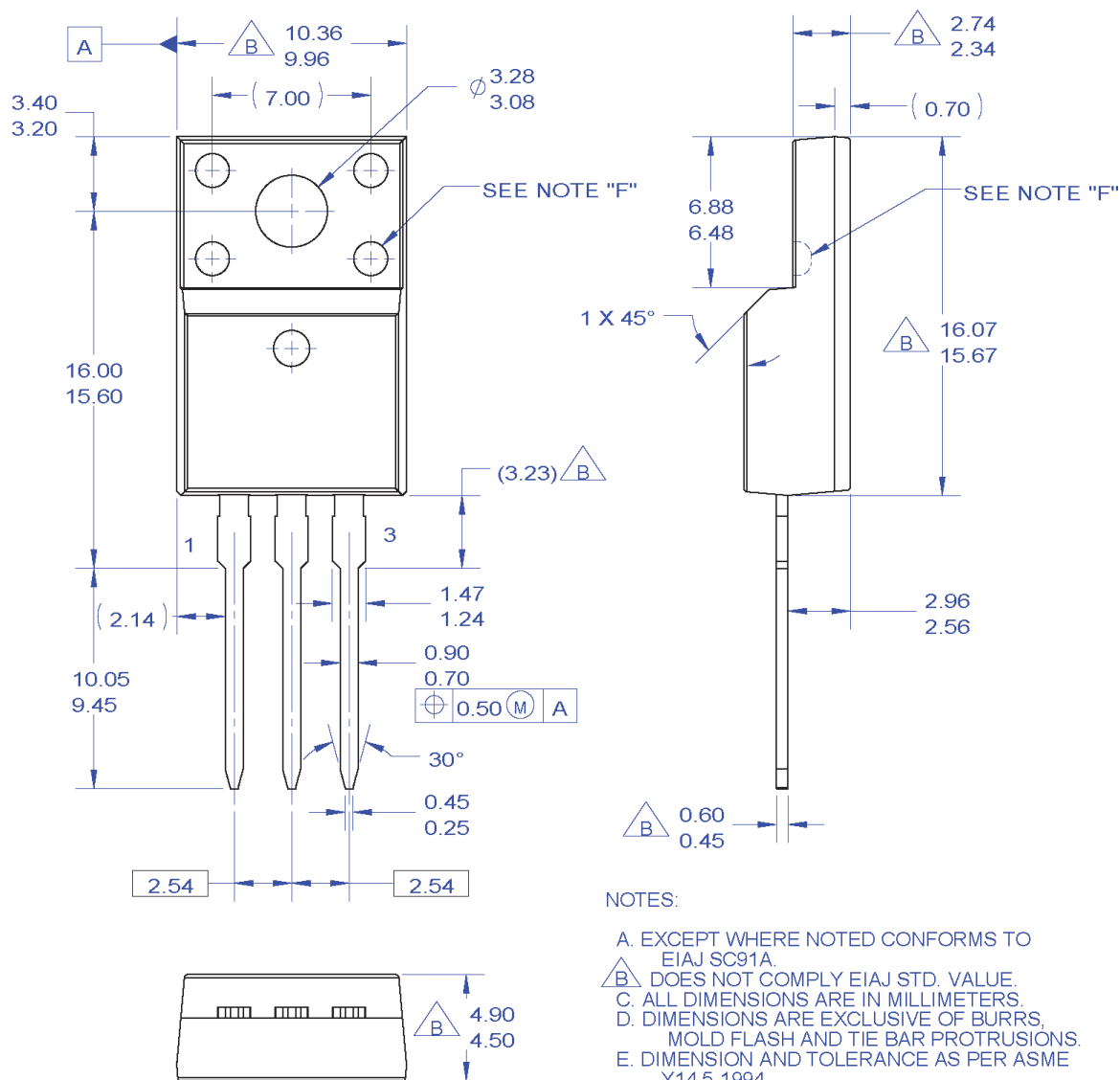
Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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Mechanical Dimensions



NOTES:

- EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- DOES NOT COMPLY EIAJ STD. VALUE.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- OPTION 1 - WITH SUPPORT PIN HOLE.
- OPTION 2 - NO SUPPORT PIN HOLE.
- DRAWING FILE NAME: TO220M03REV3

Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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